





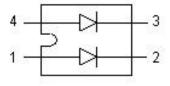
# SK2S160-100 Power Schottky Rectifier



#### **Features**

- International standard package SOT-227
- Very low VF
- Extremely low switching losses
- Low I<sub>RM</sub> -values
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

## **Circuit Diagram**



#### **Applications**

- Rectifiers in switch mode power Supplies(SMPS)
- Insulated package(V<sub>ISO</sub>=2500V<sub>RMS</sub>)
- Free wheeling diode in low voltage Converters

### **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	100	V
Average Rectified Forward Current	I <sub>F(AV)</sub>	50% duty cycle @Tc=105°C, rectangular wave form	80(Per Leg) 160(Per Device)	A
Peak One Cycle Non-Repetitive Surge Current (Per Leg)	I <sub>FSM</sub>	8.3 ms, half Sine pulse	1000	Α
Non-Repetitive Avalanche Energy(Per Leg)	E <sub>AS</sub>	T <sub>J</sub> =25°C,I <sub>AS</sub> =12A,L=180μH non repetitive	16	mJ
Total Power Dissipation	P <sub>tot</sub>	T <sub>C</sub> =25°C	150	W
Repetitive Avalanche Current (Per Leg)	I <sub>AR</sub>	Current decaying linearly to zero in 1 µsec Frequency limited by T <sub>J</sub> max.V <sub>A</sub> =1.5×V <sub>R</sub> typical	1.2	Α

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#### **Electrical Characteristics:**

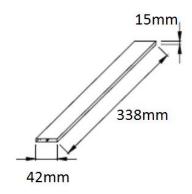
Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop(Per Leg)*	V <sub>F1</sub>	@ 80A, Pulse, T <sub>J</sub> = 25 °C	-	0.80	V
	V <sub>F2</sub>	@ 80A, Pulse, T <sub>J</sub> = 125 °C @ 160A, Pulse, T <sub>J</sub> = 125 °C	-	0.70 0.95	V
Reverse Current(Per Leg)*	I <sub>R1</sub>	$@V_R = \text{rated } V_{R_1} T_J = 25  ^{\circ}\text{C}$	-	2	mA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 125 °C	-	20	mA
Voltage Rate of Change	dv/dt	-	-	5000	V/μs

<sup>\*</sup> Pulse width < 300 µs, duty cycle < 2%

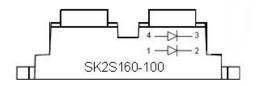
### **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-40 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-40 to +150	°C
Typical Thermal Resistance Junction to Case(Per Leg)	R <sub>0</sub> JC	DC operation	0.9	°C/W
Thermal Resistance Junction to Case(Peg Device)	R <sub>θJC</sub>	DC operation	0.5	°C/W
Mounting torque(M4)	NA		1.1-1.5/9-13	Nm/
Terminal connection torque(M4)	$M_D$	_	1.1-1.5/9-13	lb.in.
Typical Approximate Weight	wt	-	30	g

### **Tube Specification**



### **Marking Diagram**



S = SMC's Power Module
K = SOT-227 Package
2 = Circuit Configuration
S = Schottky Rectifier
160 = Forward Current (160A)
100 = Reverse Voltage (100V)

### **Ordering Information**

Device	Package	Shipping	
SK2S160-100	SOT-227 (Pb-Free)	10pcs / tube	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

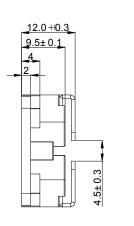
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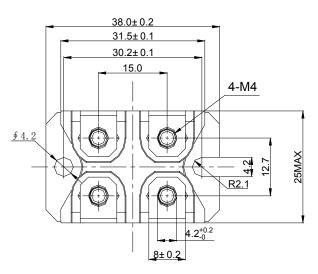


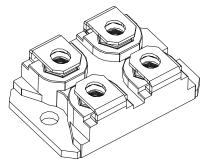




### **Mechanical Dimensions SOT-227(Millimeters)**













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